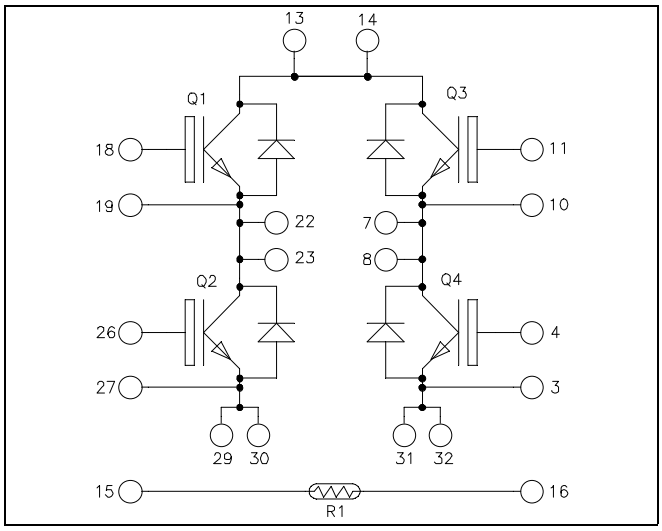
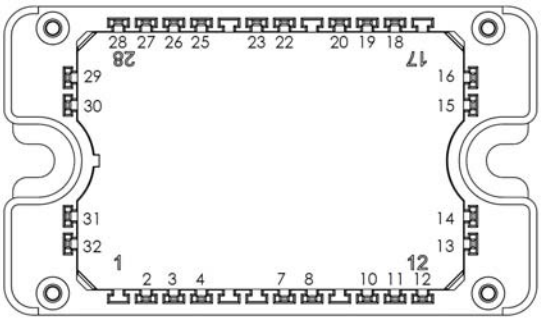
APTGT30H170T3G

Full - Bridge
Trench + Field Stop IGBT3
Power Module

V_{CES} = 1700V
I_C = 30A @ Tc = 80°C





All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 …

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- **Trench + Field Stop IGBT3**
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Voltage		1700	V
I_C	Continuous Collector Current	T_C = 25°C	45	A
		T_C = 80°C	30	
I_{CM}	Pulsed Collector Current	T_C = 25°C	70	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Power Dissipation	T_C = 25°C	210	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	60A@1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1700V				250	µA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} = 15V, I_C = 30A	T_j = 25°C		2.0	2.4	V
			T_j = 125°C		2.4		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 1.5mA		5.2	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				600	nA

Dynamic Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V f = 1MHz		2500		pF
C_{res}	Reverse Transfer Capacitance			90		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 900V I_C = 30A R_G = 18Ω		100		ns
T_r	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			650		
T_f	Fall Time			80		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 900V I_C = 30A R_G = 18Ω		100		ns
T_r	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			750		
T_f	Fall Time			100		
E_{on}	Turn-on Switching Energy			17		mJ
E_{off}	Turn-off Switching Energy			15		
R_{thJC}	Junction to Case Thermal Resistance				0.6	°C/W

Reverse diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					1700	V
I_{RM}	Reverse Leakage Current	V_R=1700V				250	µA
I_F	DC Forward Current		T_C=50°C		50		A
V_F	Diode Forward Voltage	I_F = 50A V_{GE} = 0V	T_j = 25°C		1.8	2.2	V
			T_j = 125°C		1.9		
t_{rr}	Reverse Recovery Time	I_F = 50A V_R = 900V di/dt =800A/µs	T_j = 25°C		385		ns
			T_j = 125°C		490		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		14		µC
			T_j = 125°C		23		
E_r	Reverse Recovery Energy		T_j = 25°C		6		mJ
			T_j = 125°C		12		
R_{thJC}	Junction to Case Thermal Resistance					0.7	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
$\Delta B/B$		T_C=100°C		4		%

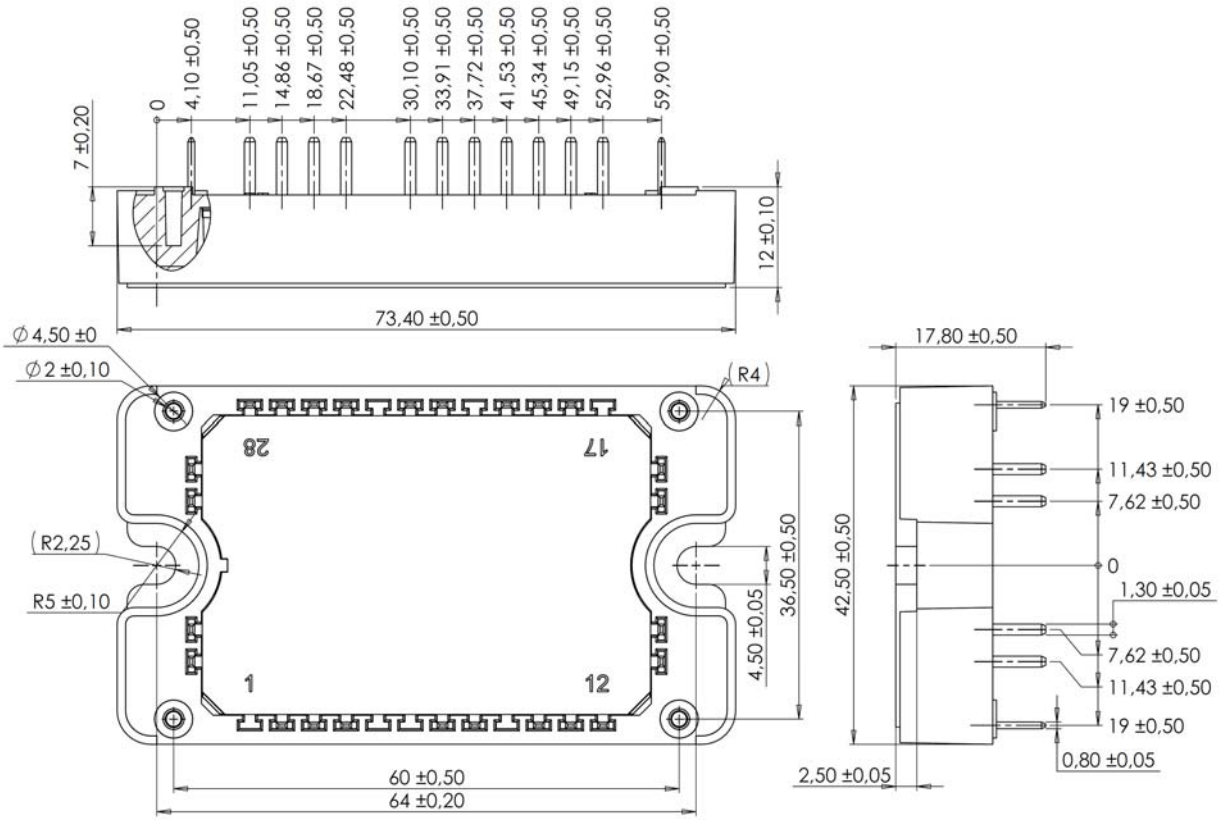
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_J	Operating junction temperature range			-40	150	°C
T_{JOP}	Recommended junction temperature under switching conditions			-40	$T_J$max -25	
T_{STG}	Storage Temperature Range			-40	125	
T_C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

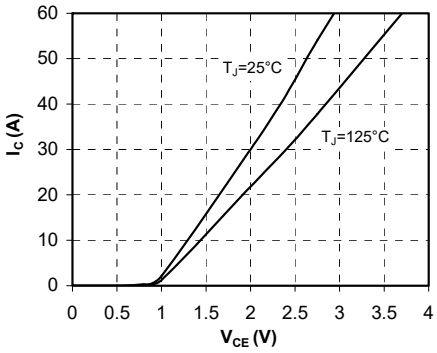
Package outline (dimensions in mm)



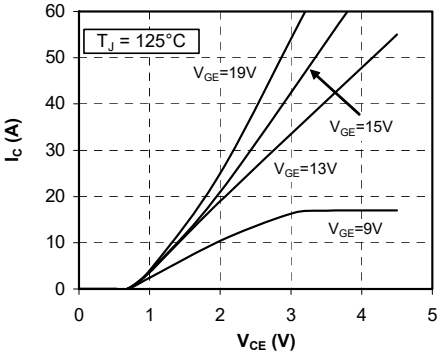
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

Typical Performance Curve

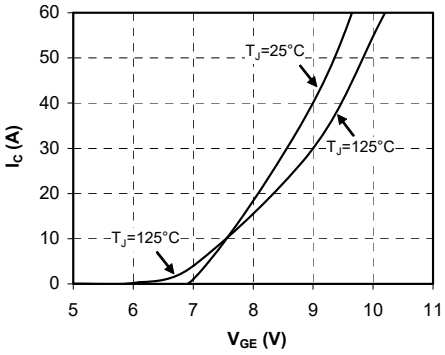
Output Characteristics (V_{GE}=15V)



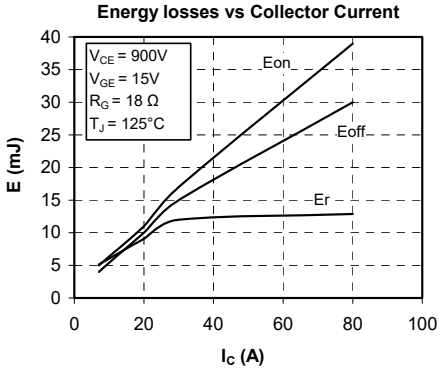
Output Characteristics



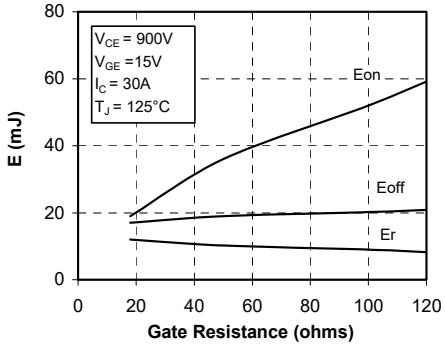
Transfert Characteristics



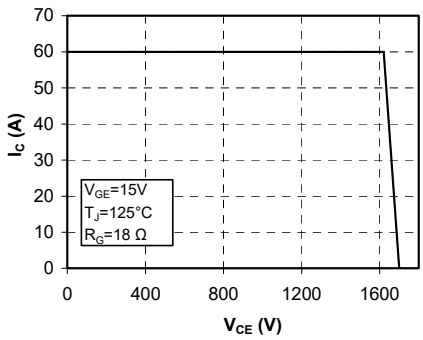
Energy losses vs Collector Current



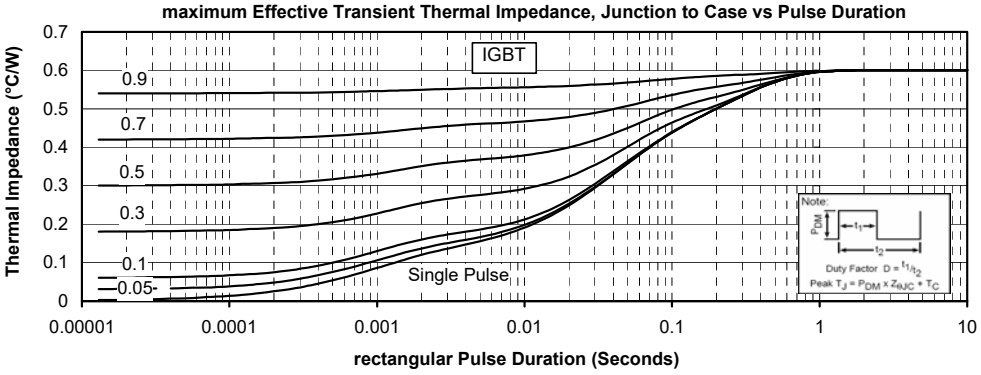
Switching Energy Losses vs Gate Resistance



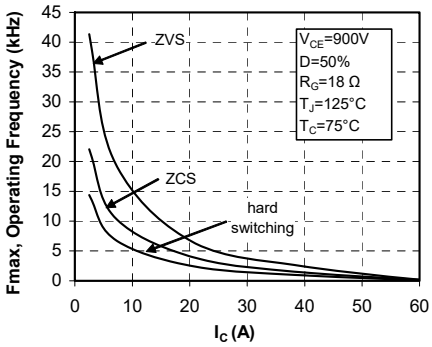
Reverse Bias Safe Operating Area



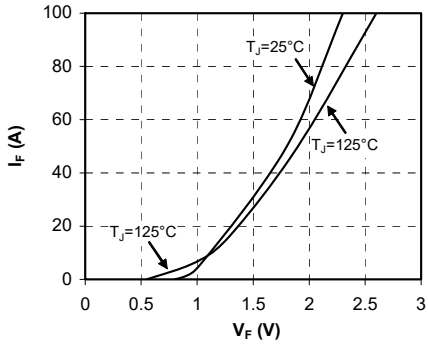
maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Operating Frequency vs Collector Current



Forward Characteristic of diode



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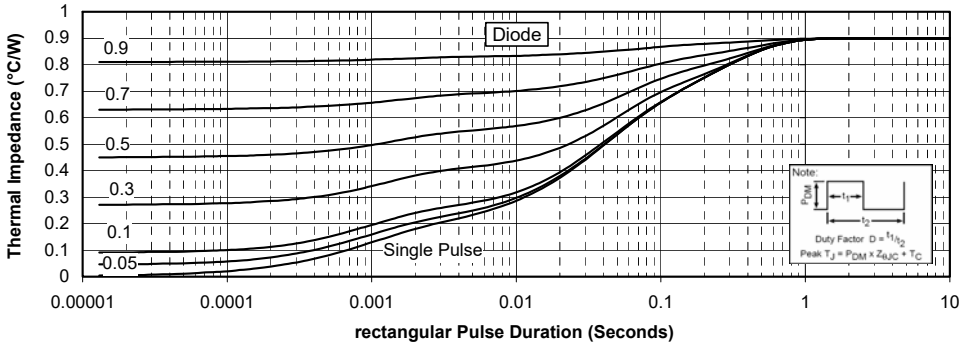

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